















**ESD** 

**TVS** 

MOS

LDO

Diode

Sensor

DC-DC

# **Product Specification**

Domestic Part Number	EV2SC3356-XXX-S1
Overseas Part Number	2SC3356-XXX
▶ Equivalent Part Number	2SC3356-XXX

"S1" means SOT-23





#### NPN Transistors

### ■ Features

- Low noise and high gain.
  NF = 1.1 dB Typ., G<sub>a</sub> = 11 dB Typ. @VcE = 10 V, Ic = 7 mA, f = 1.0 GHz
- High power gain.

MAG = 13 dB Typ. @VcE = 10 V, Ic = 20 mA, f = 1.0 GHz



# ■ Simplified outline(SOT23)

# ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	Vсво	20	V
Collector to emitter voltage	VCEO	12	V
Emitter to base voltage	VEBO	3.0	V
Collector current (DC)	Ic	100	mA
Total power dissipation	Ptot	200	mW
Junction temperature	Tj	150	$^{\circ}$
Storage temperature range	Tstg	-65 to +150	$^{\circ}$

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector- base breakdown voltage	Vсво	Ic= 100 μA, IE= 0	20			
Collector- emitter breakdown voltage		Ic= 1 mA, I <sub>B</sub> = 0	12			٧
Emitter - base breakdown voltage	VEBO	IE= 100 uA, IC= 0	3			
Collector-base cut-off current	Ісво	Vcb= 10 V , IE= 0			1	uA
Emitter cut-off current	ІЕВО	VEB= 3V , IC=0			1	uA
Collector-emitter saturation voltage *	VCE(sat)	at) Ic=50 mA, IB=5mA			0.4	V
Base - emitter saturation voltage *	VBE(sat)	Ic=50 mA, Iв=5mA			1.2	V
DC current gain *	hfe	VcE= 10V, Ic= 20mA	50		400	
Insertion power gain	S21e   ²	VcE = 10 V, Ic = 20 mA, f= 1GHz		11.5		dB
Noise figure	NF	VcE = 10 V, Ic = 7 mA, f= 1GHz		1.1	2	ub
Reverse transfer capacitance	Cre	Vcb= 10V, IE= 0,f=1MHz		0.55	1	pF
Transition frequency	f⊤	VcE= 10V, Ic= 20mA		7		GHz

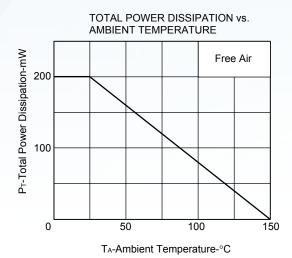
<sup>\*.</sup> Pulse measurement: PW  $\leqslant$  350  $\,\mu$  s, Duty Cycle  $\leqslant$  2%.

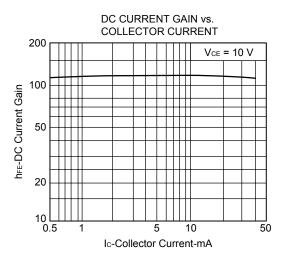
#### ■ hFE Classification

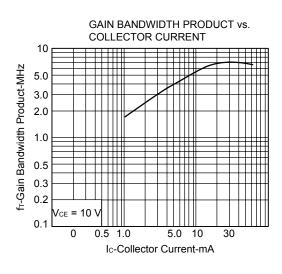
Туре	EV2SC3356-R23-S1	EV2SC3356-R24-S1	EV2SC3356-R25-S1	EV2SC3356-R26-S1		
Range	50-100	80-160	125-250	250-400		
Marking	R23	R24	R25	R26		

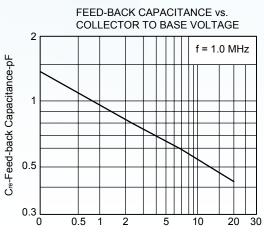


## ■ Typical Characterisitics

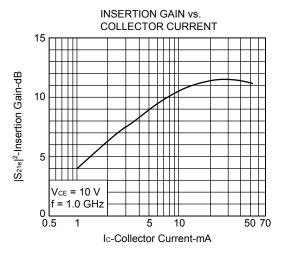


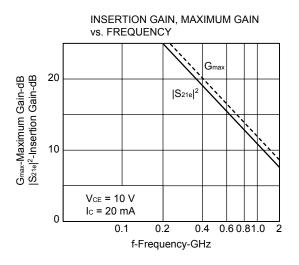






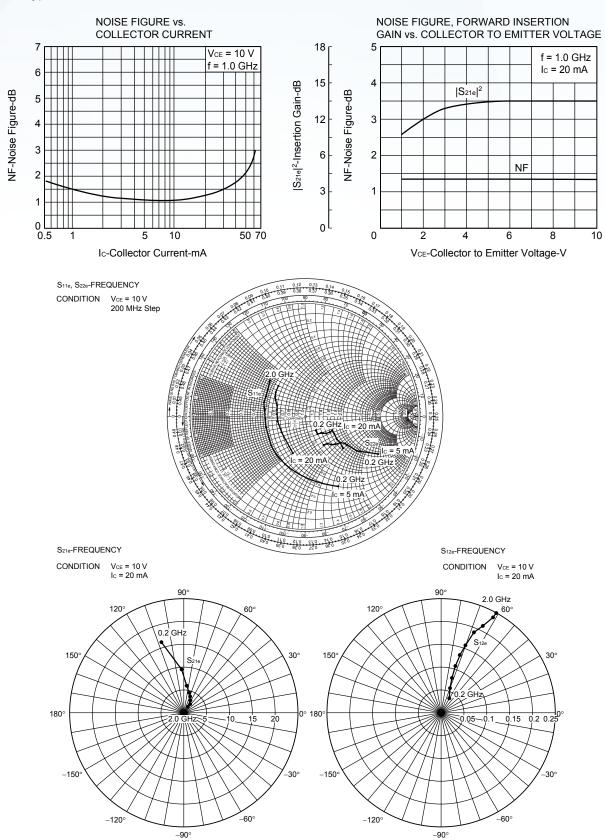
Vcb-Collector to Base Voltage-V





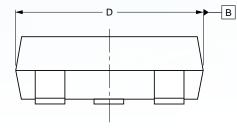


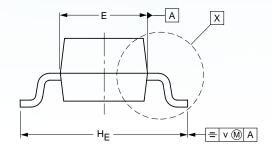
# ■ Typical Characterisitics

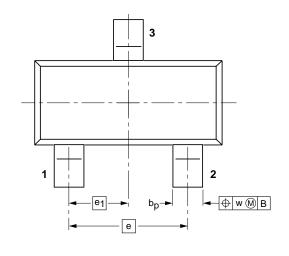


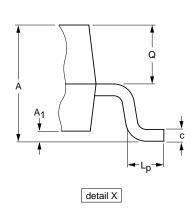


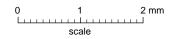
# ■ SOT-23











# **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub> max.	bp	С	D	Е	e	e <sub>1</sub>	HE	L <sub>p</sub>	q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1



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